



DNLS320E

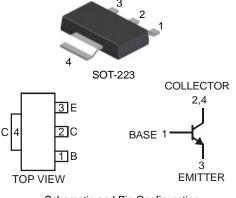
LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Resistance R_{CE(SAT)} = 80mΩ at 3A
- High DC Current Gain $h_{FE} > 400$ at $I_C = 2A$
- Complementary PNP Type Available (DPLS325E)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	20	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	5	V
Continuous Collector Current	Ι _C	3	А
Peak Pulse Current	I _{CM}	8	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation $@T_A = 25^{\circ}C$ (Note 3)	PD	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) $@T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

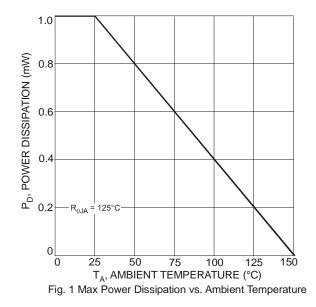
 Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

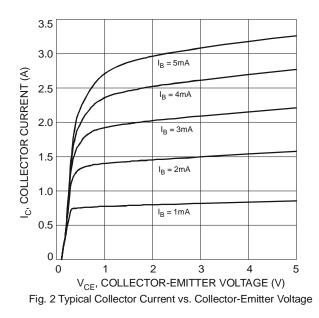


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Off Characteristics						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	20	_	_	V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	20	_	_	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	_	_	V	$I_{\rm E} = 100 \mu A, I_{\rm C} = 0$
Collector Cutoff Current	I _{CBO}		_	100	nA	$V_{CB} = 16V, I_E = 0$
Emitter Cutoff Current	I _{EBO}			100	nA	$V_{EB} = 4V, I_{C} = 0$
On Characteristics (Note 4)				•	•	·
		_	0.04	0.10		$I_{C} = 0.1A, I_{B} = 0.5mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.18	0.50	V	$I_{\rm C} = 2A, I_{\rm B} = 10 {\rm mA}$
		_	0.24	0.45		$I_{C} = 3A, I_{B} = 20mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	0.9	V	$I_{\rm C} = 1$ A, $I_{\rm B} = 10$ mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	_	0.9	V	$V_{CE} = 2V, I_C = 1A$
		500	_	_		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	h _{FE}	400	—		—	$V_{CE} = 2V, I_C = 2A$
		150	_			$V_{CE} = 2V, I_C = 6A$
AC Characteristics			-			
Transition Frequency	f _T	150	_		MHz	$V_{CE} = 5V, I_{C} = 50mA, f = 50MHz$
Input Capacitance	Cibo		230	—	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}		23		pF	$V_{CB} = 10V, f = 1MHz$
Switching Timos	t _{on}		26		ns	$V_{CC} = 10V, I_{C} = 500mA$
Switching Times	toff		220		ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

Notes: 4. Pulse Test: Pulse width \leq 300 μ s. Duty cycle \leq 2.0%.







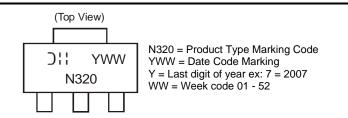
2,000 0.5 200 V_{CE(SAT)}, COLLECTOR-EMITTER SATURATION VOLTAGE (V) 0.4 1,500 h_{FE}, DC CURRENT GAIN 150°d 0.3 т_А = 85°С 1,000 $T_A = 25^{\circ}C$ 0.2 T_A 85 500 $T_A = -55^{\circ}C$ 0.1 25°C = -55°C 0 0 0.001 0.001 0.01 0.1 0.01 0.1 10 10 1 I_C, COLLECTOR CURRENT (A) Fig. 4 Typical Collector-Emitter Saturation Voltage I_C, COLLECTOR CURRENT (A) Fig. 3 Typical DC Current Gain vs. Collector Current vs. Collector Current 1.2 1.2 V_{BE(SAT)}, BASE-EMITTER SATURATION VOLTAGE (V) V_{BE(ON)}, BASE-EMITTER TURN-ON VOLTAGE (V) 200 1.0 1.0 0.8 0.8 0.6 0.6 0.4 0.4 = 85°C TA 0.2 0.2 T 50 0 0 0.001 0.01 0.1 1 10 0.001 0.01 0.1 1 10 I_C, COLLECTOR CURRENT (A) I_C, COLLECTOR CURRENT (A) Fig. 6 Typical Base-Emitter Saturation Voltage Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DNLS320E-13	SOT-223	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap2007.pdf.

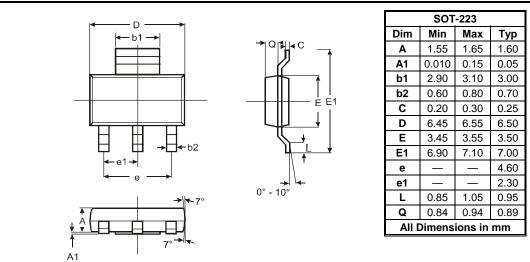
Marking Information



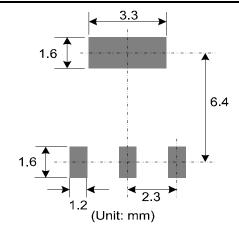
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Package Outline Dimensions



Suggested Pad Layout:



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